



100V P-Channel Enhancement Mode MOSFET

Voltage

-100 V

Current

-5 A

Features

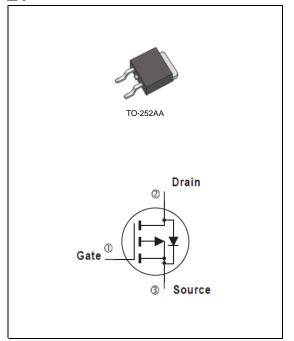
- R_{DS(ON)}, V_{GS}@-10V,I_D@-2.5A<650mΩ
- $R_{DS(ON)}$, $V_{GS}@-4.5V$, $I_D@-2A<700m\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)



• Case: TO-252AA Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0104 ounces, 0.297grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMET	ER	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	-100	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C	· I _D	-5	A	
	T _C =100°C		-3.1		
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	-10		
Power Dissipation	T _C =25°C	Po	30	W	
	T _C =100°C		12		
Continuous Drain Current	T _A =25°C	I _D	-1.3	Α	
	T _A =70°C		-1.1	Α	
Power Dissipation	T _A =25°C	ľ	2.0	W	
Power Dissipation	T _A =70°C	Pb	1.3		
Single Pulse Avalanche Energy (Note 6)		E _{AS}	1.3	mJ	
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	4.2	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =-250uA	-100	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250$ uA	-1.0	-2.0	-2.5	V	
Drain-Source On-State Resistance	В	V _{GS} =-10V,I _D =-2.5A	-	500	650	mΩ	
Drain-Source On-State Resistance	$R_{DS(on)}$	V _{GS} =-4.5V,I _D =-2A	-	560	700		
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =-80V, V_{GS} =0V	-	-	-1.0	uA	
Gate-Source Leakage Current	I_{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA	
Dynamic (Note 5)							
Total Gate Charge	Q_g	V _{DS} =-50V, I _D =-5A, V _{GS} =-10V ^(Note 1,2)	-	8	-	nC	
Gate-Source Charge	Q_gs		-	1.8	-		
Gate-Drain Charge	Q_gd		-	1.4	-		
Input Capacitance	Ciss	V _{DS} =-15V, V _{GS} =0V, f=1.0MHZ	-	448	-	pF	
Output Capacitance	Coss		-	28	-		
Reverse Transfer Capacitance	Crss	I=1.0IVIIIZ	-	21	-		
Turn-On Delay Time	td _(on)	V 50V DI 40C	-	3.7	-	ns	
Turn-On Rise Time	t _r	V_{DS} =-50V,RL=10 Ω ,	-	25	-		
Turn-Off Delay Time	td _(off)	V_{GS} =-10V, R_G =6.2 Ω (Note 1,2)	-	21	-		
Turn-Off Fall Time	t _f		-	22	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	ı				-5	Α	
Diode Forward Current	I _S		-	-	-:o	^	
Reverse Recovery Time	V_{SD}	I _S =-1A,V _{GS} =0V	_	-0.8	-1.2	V	

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited
- 5. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper
- 6. L=0.1mH, I_{AS} =-5A, V_{GS} =-10V, V_{DS} =-25V, R_{G} =25 ohm, Starting T_{J} =25°C
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

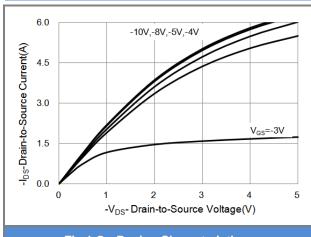


Fig.1 On-Region Characteristics

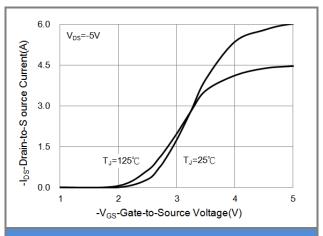


Fig.2 Transfer Characteristics

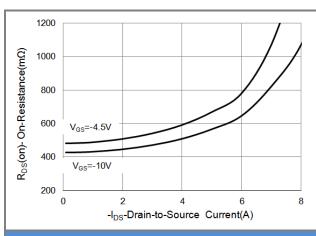


Fig.3 On-Resistance vs. Drain Current

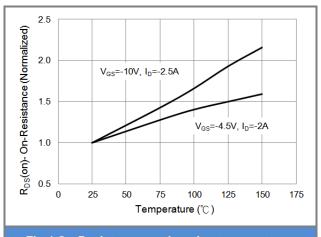


Fig.4 On-Resistance vs. Junction temperature

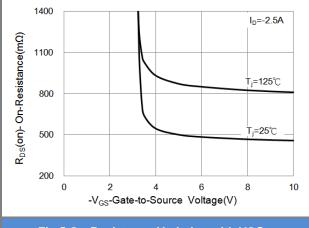


Fig.5 On-Resistance Variation with VGS.

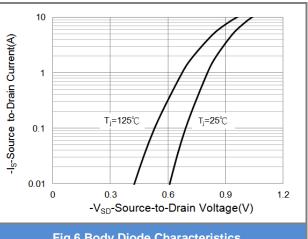


Fig.6 Body Diode Characteristics





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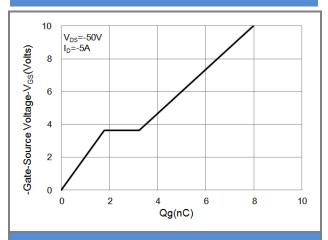


Fig.7 Gate-Charge Characteristics

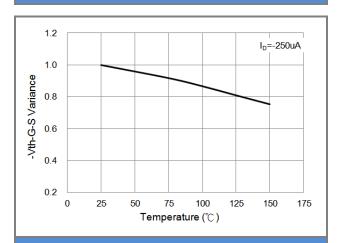
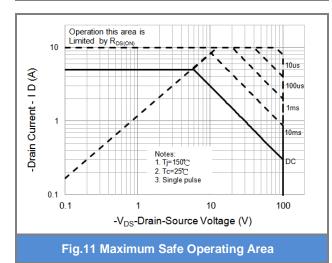


Fig.9 Threshold Voltage Variation with Temperature



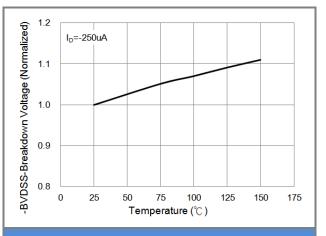


Fig.8 Breakdown Voltage Variation vs. Temperature

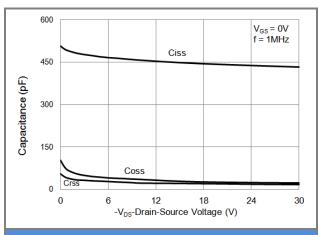


Fig.10 Capacitance vs. Drain-Source Voltage





TYPICAL CHARACTERISTIC CURVES

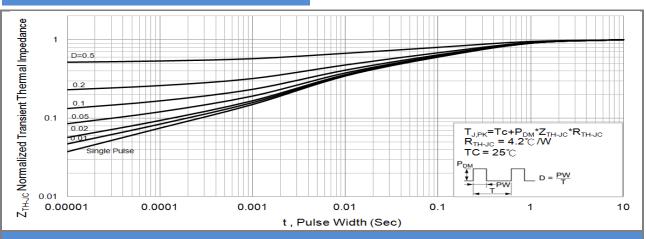
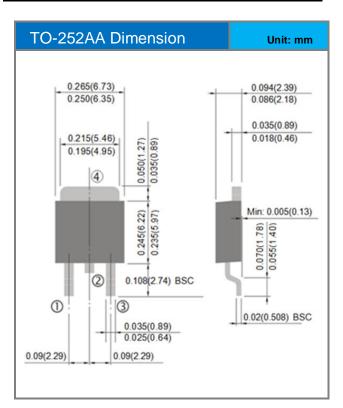


Fig.12 Normalized Thermal Transient Impedance





Packaging Information



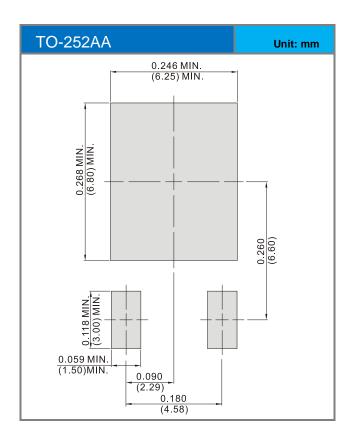




PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJD5P10A_L2_00001	TO-252AA	3,000pcs / 13" reel	D5P10A	Halogen free

MOUNTING PAD LAYOUT







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